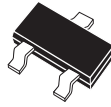


CMPT3410

**SURFACE MOUNT
NPN SILICON
LOW $V_{CE(SAT)}$ TRANSISTOR**



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT3410 type is a NPN Low $V_{CE(SAT)}$ silicon transistor manufactured by the epitaxial planar process and epoxy molded in an SOT-23 surface mount package. This device is designed for battery driven, handheld devices requiring high current and Low $V_{CE(SAT)}$ voltages.

MARKING CODE: C341

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	1.0	A
Collector Current (Peak)	I_{CM}	1.5	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

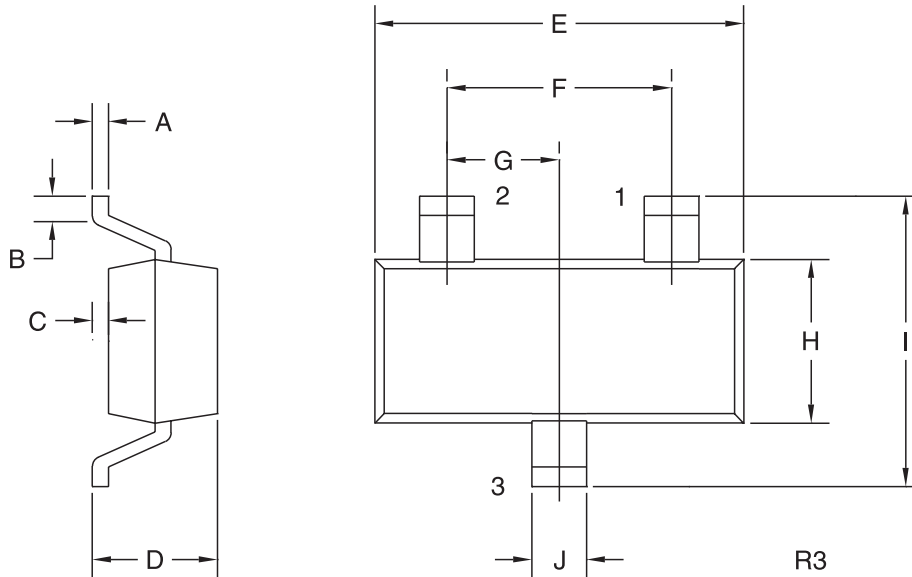
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=40\text{V}$			100	nA
I_{EBO}	$V_{EB}=6.0\text{V}$			100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	40			V
BV_{CEO}	$I_C=10\text{mA}$	25			V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0			V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		20	50	mV
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		35	75	mV
$V_{CE(SAT)}$	$I_C=200\text{mA}, I_B=20\text{mA}$		75	150	mV
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		130	250	mV
$V_{CE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$		200	400	mV
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		250	450	mV
$V_{BE(SAT)}$	$I_C=800\text{mA}, I_B=80\text{mA}$			1.1	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$			0.9	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100			
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	100		300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	100			
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$	50			
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	100			MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$			10	pF

R0 (15-November 2004)

**SURFACE MOUNT
NPN SILICON
LOW V_{CE} (SAT) TRANSISTOR**

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: C341

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)